

Isc N-Channel MOSFET Transistor

STF22NM60N

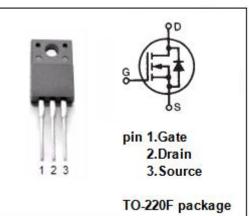
• FEATURES

- · Low input capacitance and gate charge
- · Low gate input resistances
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

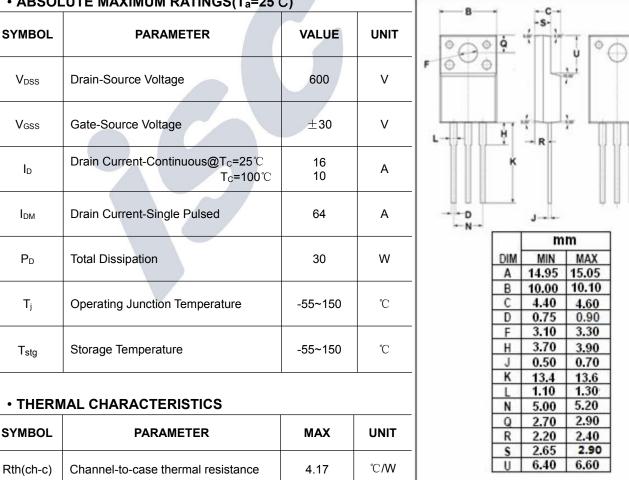
APPLICATIONS

Switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	600			v
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	2		4	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =8A		200	220	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±25V;V _{DS} = 0V			±0.1	μ Α
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25℃ T _J =125℃			1 100	μ Α
VSDF	Diode forward voltage	I _{SD} =16A, V _{GS} = 0 V			1.6	v

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